

U.S.S.N. 10/813,786

Claim Amendments

Please amend claims 1, 4-6, 12-15, 17, and 18 as follows:

Please cancel claims 16, and 19-20 as follows:

Please add new claims 21-23 as follows:

Claims as Amended

1. (currently amended) A method for forming a gate dielectric layer comprising:

providing a semiconductor substrate;

thermally oxidizing the semiconductor substrate within a first thermal oxidizing atmosphere comprising a halogen getter material to form a first gate dielectric layer ~~upon~~ comprising a once thermally oxidized semiconductor substrate; and,

thermally oxidizing the once thermally oxidized semiconductor substrate within a second thermal oxidizing atmosphere not comprising a halogen getter material to form a second gate dielectric layer on the first dielectric layer.

2. (original) The method of claim 1 wherein the semiconductor

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substrate is a silicon semiconductor substrate.

3. (original) The method of claim 1 wherein the semiconductor substrate is a silicon-germanium alloy semiconductor substrate.

4. (currently amended) The method of claim 1 wherein the first gate dielectric layer is formed from a non-nitrided silicon oxide material.

5. (currently amended) The method of claim 1 wherein the halogen getter material ~~is a~~ comprises chlorine ~~halogen getter material~~.

6. (currently amended) The method of claim 5 wherein the ~~chlorine~~ halogen getter material is selected from the group consisting of chlorine, hydrogen chloride, and one to three carbon atom chlorocarbons and hydrochlorocarbons.

7. (original) The method of claim 1 wherein the thermal oxidizing atmosphere is selected from the group consisting of wet thermal oxidizing atmospheres and dry thermal oxidizing atmospheres.

8. (original) A method for forming a gate dielectric layer comprising:

providing a semiconductor substrate;

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thermally oxidizing the semiconductor substrate within a first thermal oxidizing atmosphere comprising a halogen getter material to form a first gate dielectric layer upon a once thermally oxidized semiconductor substrate; and

thermally oxidizing the once thermally oxidized semiconductor substrate within a second thermal oxidizing atmosphere not comprising a halogen getter material to form a second gate dielectric layer over a twice thermally oxidized semiconductor substrate.

9. (original) The method of claim 8 wherein the semiconductor substrate is a silicon semiconductor substrate.

10. (original) The method of claim 8 wherein the semiconductor substrate is a silicon-germanium alloy semiconductor substrate.

11. (currently amended) The method of claim 8 wherein the first gate dielectric layer ~~is formed from~~ comprises a non-nitrided silicon oxide material.

12. (currently amended) The method of claim 8 wherein the second gate dielectric layer ~~is formed from~~ comprises a nitrided silicon oxide material.

13. (currently amended) The method of claim 8 wherein the halogen getter material ~~is a~~ comprises chlorine halogen getter

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material.

14. (currently amended) The method of claim 13 wherein the ~~chlorine~~ halogen getter material is selected from the group consisting of chlorine, hydrogen chloride, and one to three carbon atom chlorocarbons and hydrochlorocarbons.

15. (currently amended) The method of claim 8 wherein the first and second thermal oxidizing atmospheres ~~is~~ are selected from the group consisting of wet thermal oxidizing atmospheres and dry thermal oxidizing atmospheres.

16. cancelled

17. (currently amended) The method of claim 8 wherein the first gate dielectric layer is stripped ~~from~~ over a portion of the once thermally oxidized semiconductor substrate prior to forming the second gate dielectric layer ~~over the twice thermally oxidized semiconductor substrate.~~

18. (currently amended) The method of claim 8 wherein the second gate dielectric layer is formed upon the first gate dielectric layer ~~which is formed upon the twice thermally oxidized semiconductor substrate.~~

Claims 19-20 cancelled

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21. (new) The method of claim 1 wherein the first gate dielectric layer is stripped over a portion of the semiconductor substrate comprising a second active region prior to forming the second gate dielectric layer, said second gate dielectric layer formed to comprise a bilayer gate dielectric on a first active region and formed to comprise a single layer gate dielectric on the second active region.

22. (new) The method of claim 1 wherein the second gate dielectric layer comprises a nitrided silicon oxide material.

23. (new) The method of claim 1 wherein the first gate dielectric layer is stripped over a portion of the semiconductor substrate comprising a second active region prior to forming the second gate dielectric layer, said second gate dielectric layer formed to comprise a bilayer gate dielectric on a first active region and formed to comprise a single layer gate dielectric on the second active region.